



New Product

Si4433DY
Vishay Siliconix

P-Channel 1.8-V (G-S) MOSFET

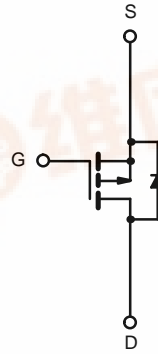
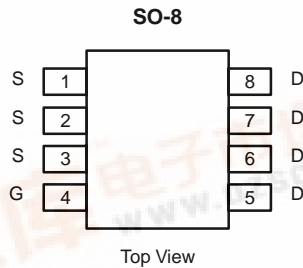
PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-20	0.110 @ $V_{GS} = -4.5$ V	-3.9
	0.160 @ $V_{GS} = -2.5$ V	-3.2
	0.240 @ $V_{GS} = -1.8$ V	-2.6

FEATURES

- TrenchFET® Power MOSFET
- Fast Switching

APPLICATION

- DC-DC Conversion
- Asynchronous Buck Converter
- Voltage Inverter



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)					
Parameter	Symbol	10 secs	Steady State	Unit	
Drain-Source Voltage	V_{DS}	-20		V	
Gate-Source Voltage	V_{GS}	± 8			
Continuous Drain Current ($T_J = 150^\circ\text{C}$) ^a	I_D	$T_A = 25^\circ\text{C}$	-3.9	-2.9	A
		$T_A = 85^\circ\text{C}$	-2.8	-2.1	
Pulsed Drain Current	I_{DM}	-10			
Continuous Source Current (Diode Conduction) ^a	I_S	-2.1	-1.2		
Maximum Power Dissipation ^a	P_D	$T_A = 25^\circ\text{C}$	2.5	1.4	W
		$T_A = 85^\circ\text{C}$	1.3	0.7	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to 150		$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	R_{thJA}	$t \leq 10$ sec	40	50	$^\circ\text{C}/\text{W}$
		Steady State	75	90	
Maximum Junction-to-Foot (Drain)	R_{thJF}	19	25		

Notes:
a. Surface Mounted on 1" x 1" FR4 Board.

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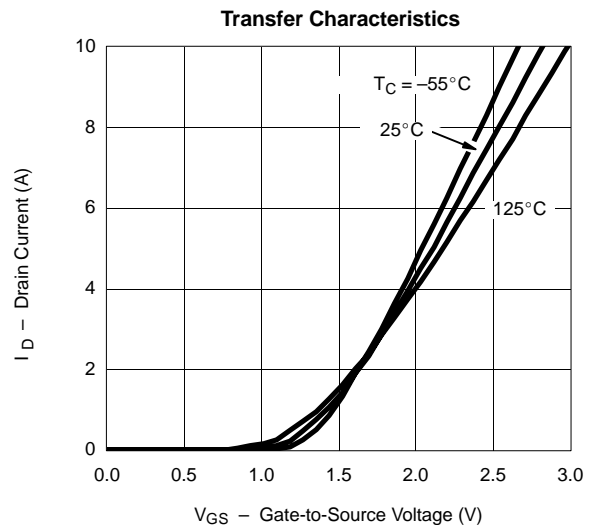
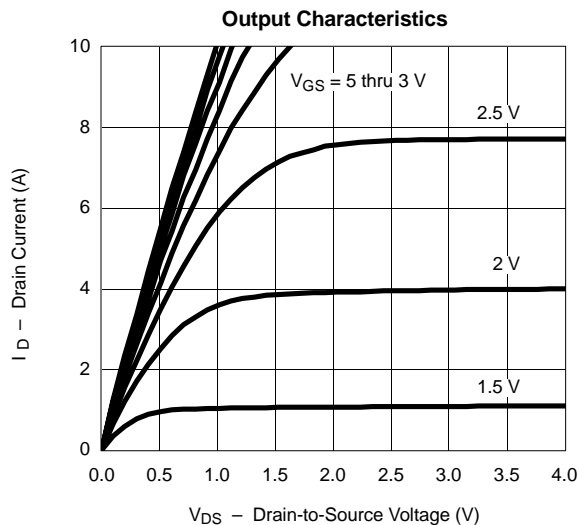


SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = -250 μA	-0.45			V
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±8 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = -16 V, V _{GS} = 0 V			-1	μA
		V _{DS} = -16 V, V _{GS} = 0 V, T _J = 85 °C			-5	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≤ -5 V, V _{GS} = -4.5 V	-10			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = -4.5 V, I _D = -2.7 A		0.095	0.110	Ω
		V _{GS} = -2.5 V, I _D = -2.2 A		0.137	0.160	
		V _{GS} = -1.8 V, I _D = -1 A		0.205	0.240	
Forward Transconductance ^a	g _{fs}	V _{DS} = -10 V, I _D = -2.7 A		7		S
Diode Forward Voltage ^a	V _{SD}	I _S = -0.9 A, V _{GS} = 0 V		-0.8	-1.2	V
Dynamic^b						
Total Gate Charge	Q _g	V _{DS} = -10 V, V _{GS} = -4.5 V, I _D = -2.7 A		4.4	6.5	nC
Gate-Source Charge	Q _{gs}			1.4		
Gate-Drain Charge	Q _{gd}			0.65		
Turn-On Delay Time	t _{d(on)}	V _{DD} = -10 V, R _L = 10 Ω I _D ≅ -1 A, V _{GEN} = -4.5 V, R _G = 6 Ω		16	25	ns
Rise Time	t _r			30	45	
Turn-Off Delay Time	t _{d(off)}			30	45	
Fall Time	t _f			27	40	
Source-Drain Reverse Recovery Time	t _{rr}		I _F = -0.9 A, di/dt = 100 A/μs		20	

Notes

- a. Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- b. Guaranteed by design, not subject to production testing.

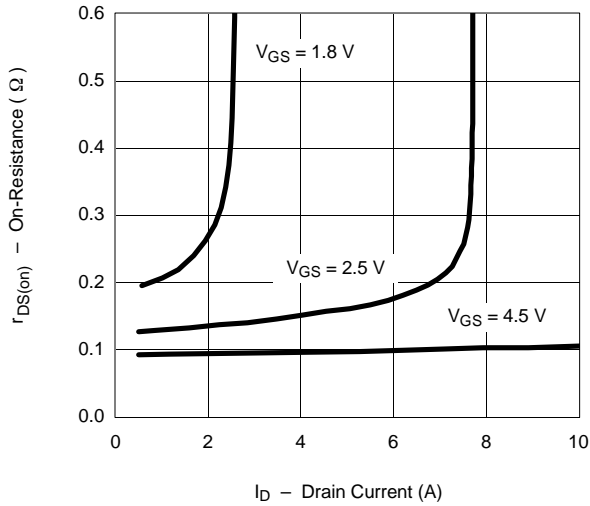
TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)



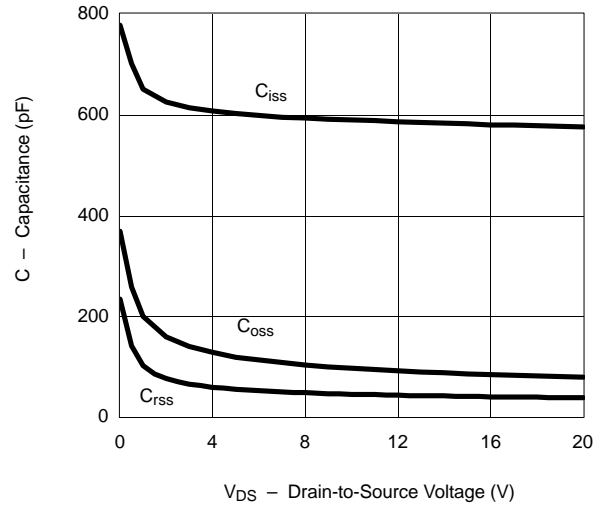


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

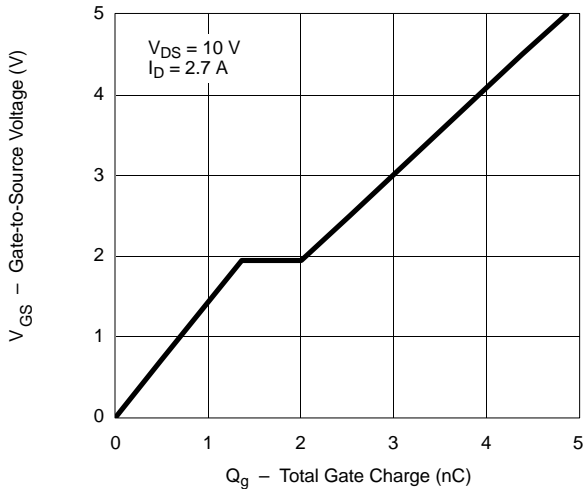
On-Resistance vs. Drain Current



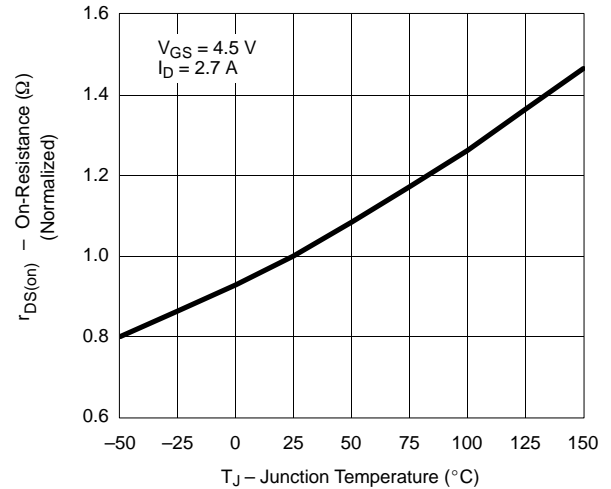
Capacitance



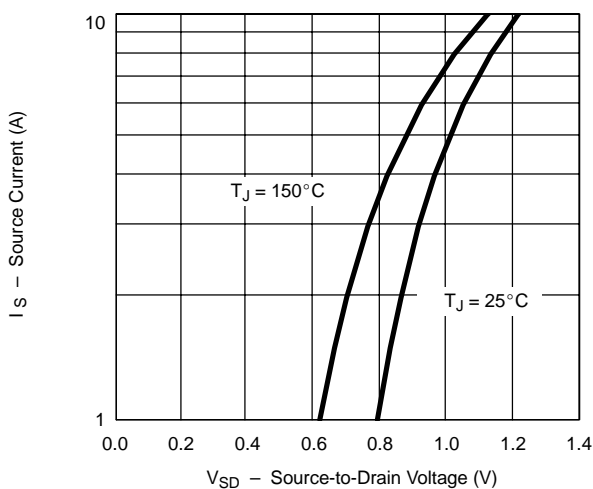
Gate Charge



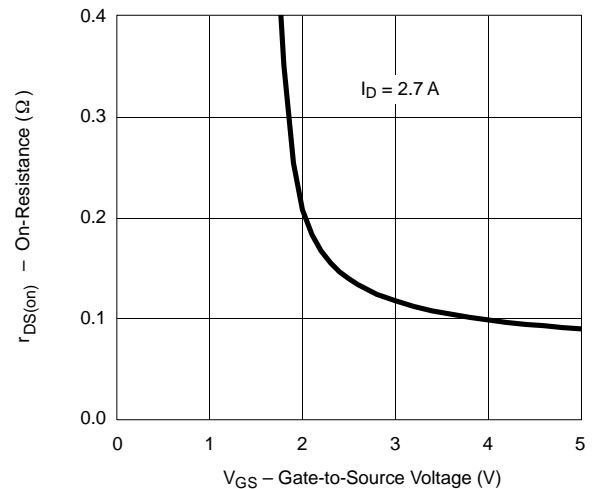
On-Resistance vs. Junction Temperature



Source-Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage





TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

